# 2SD1420

## Silicon NPN Epitaxial

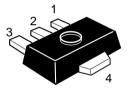
# **HITACHI**

### **Application**

Low frequency power amplifier

#### Outline

UPAK



- 1. Base
- 2. Collector
- 3. Emitter
- 4. Collector (Flange)



## 2SD1420

### **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{\text{CBO}}$	180	V
Collector to emitter voltage	V <sub>CEO</sub>	120	V
Emitter to base voltage	$V_{EBO}$	5	V
Collector current	I <sub>c</sub>	1.5	A
Collector peak current	i <sub>C(peak)</sub> *1	3	A
Collector power dissipation	P <sub>C</sub> *2	1	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW ≤ 10 ms, Duty cycle ≤ 20%

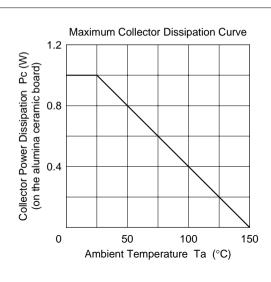
2. Value on the alumina ceramic board (12.5 x 20 x 0.7 mm)

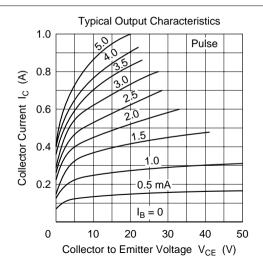
### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

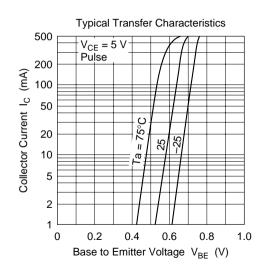
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	180	_	_	V	$I_{\rm C} = 1 \text{ mA}, I_{\rm E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	120	_	_	V	$I_{C}$ = 10 mA, $R_{BE}$ = $\infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_{E} = 1 \text{ mA}, I_{C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	10	μΑ	$V_{CB} = 160 \text{ V}, I_{E} = 0$
DC current transfer ratio	h <sub>FE1</sub> *1	60	_	320		$V_{CE} = 5 \text{ V}, I_{C} = 0.15 \text{ A}$
	h <sub>FE2</sub>	30	_	_		$V_{CE} = 5 \text{ V}, I_{C} = 0.5 \text{ A}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1.0	V	$I_C = 0.5 \text{ A}, I_B = 50 \text{ mA}, \text{ Pulse}$
Base to emitter voltage	$V_{BE}$	_	_	0.9	V	$V_{CE} = 5 \text{ V}, I_{C} = 0.15 \text{ A}, \text{ Pulse}$

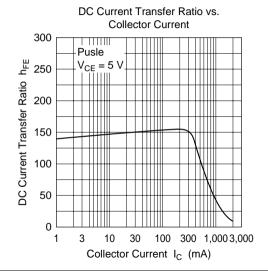
Note: 1. The 2SD1420 is grouped by  $h_{\text{FE1}}$  as follows.

Mark	EA	EB	EC
h <sub>FE1</sub>	60 to 120	100 to 200	160 to 320

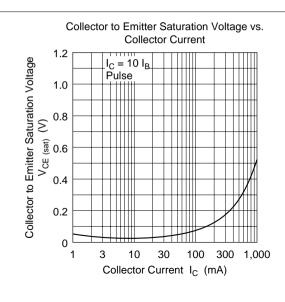


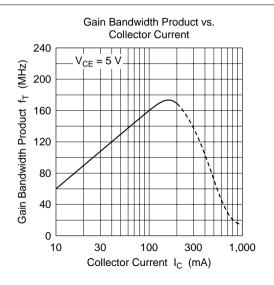


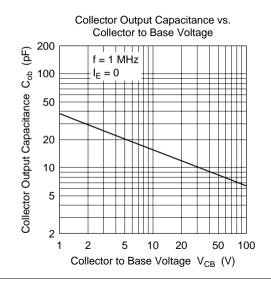




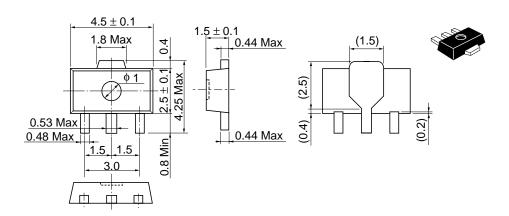
## 2SD1420







Unit: mm



Hitachi Code	UPAK
JEDEC	_
EIAJ	Conforms
Weight (reference value)	0.050 g

#### **Cautions**

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